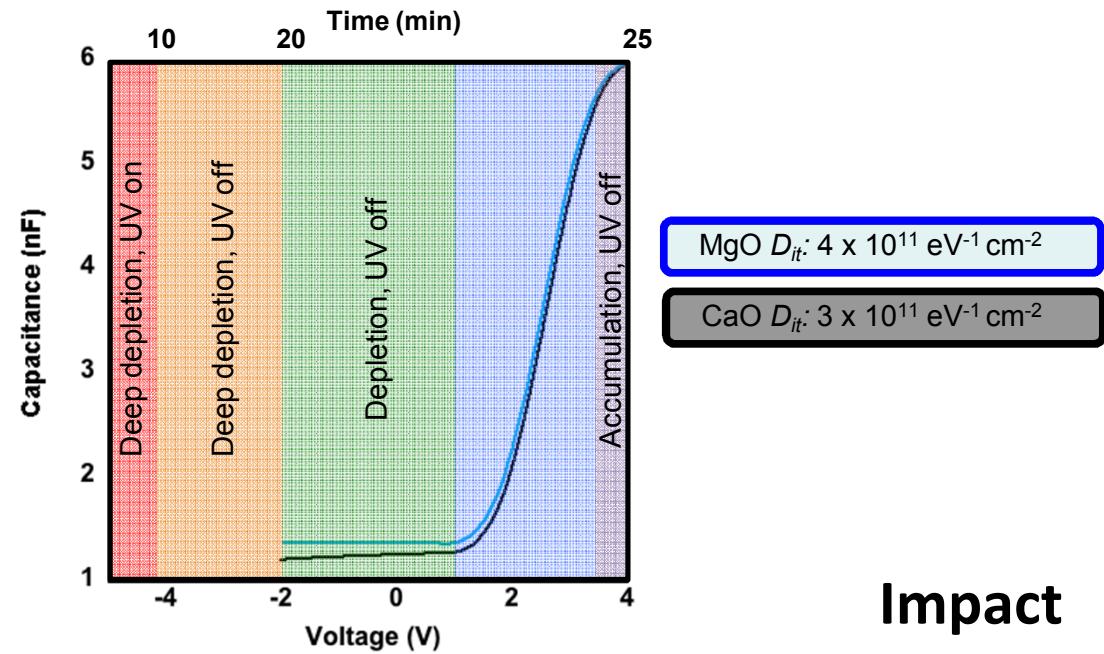


Reliable High-Performance Gate

Oxides for Wide Band Gap Devices

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Impact

- Increased System Performance, Efficiency, and Reliability
- Reduced System Cost
- Reduced Power Electronics Size

Purpose

- Gate dielectrics are a key limiter in GaN- and SiC-based power electronics technology
- Engineered gates will enable the development of robust and reliable MOSFETs and MOSHEMTs